Ordering number : ENA1473

SANYO Semiconductors
DATA SHEET

LE25LA642CS — 64Kbit Serial SPI EEPROM (SPI Bus)

Overview

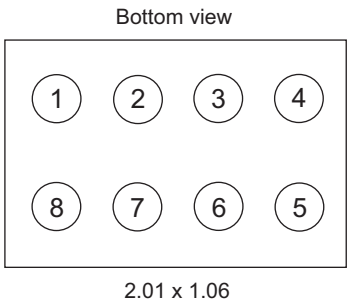
The LE25LA642CS is a 64Kbit EEPROM that supports serial peripheral interface (SPI). It realizes high speed operation and high level reliability by incorporating SANYO's high performance CMOS EEPROM technology. The interface is compatible with SPI bus protocol, therefore, it is best suited for applications that require small-scale rewritable nonvolatile parameter memory. Moreover, the LE25LA642CS has a 32 bytes page rewrite function that provides rapid data rewriting.

Features

- Capacity : 64Kbits (8K×8bits)
- Single supply voltage : 1.8V to 3.6V
- Serial interface : SPI Mode0, Mode3 supported
- Operating clock frequency : 5MHz (2.5V to 3.6V), 3MHz (1.8V to 3.6V)
- Low current dissipation : Standby : 2μA (max.)
  : Active (Read) : 3mA (max.)
  : Active (Rewrite) : 3mA (max.)
- Page write function : 32bytes
- Rewrite time : 10ms
- Number of rewrite times : 10^5 times/Page write
- Data retention period : 20years
- High reliability : Adopts SANYO's proprietary symmetric memory array configuration (USP6947325)
  Incorporates a feature to prohibit write operations under low voltage conditions.

* This product is licensed from Silicon Storage Technology, Inc. (USA), and manufactured and sold by SANYO Semiconductor Co., Ltd.

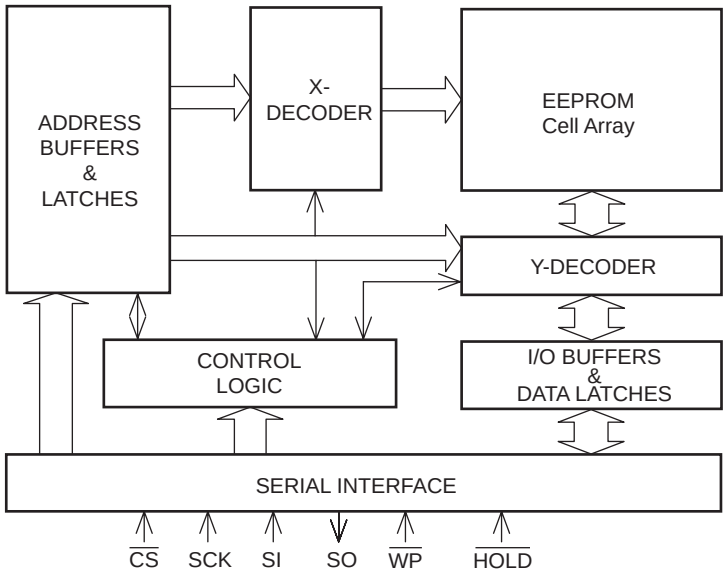
Pin Assignment



Pin Descriptions

PIN.1	$\overline{WP}$	Write protect
PIN.2	V_{SS}	Ground
PIN.3	V_{DD}	Power supply
PIN.4	$\overline{CS}$	Chip select
PIN.5	$\overline{HOLD}$	Hold
PIN.6	SO	Serial data output
PIN.7	SI	Serial data input
PIN.8	SCK	Serial clock

Block Diagram



Specifications

Absolute Maximum Rating/If an electrical stress exceeding the maximum rating is applied, the device may be damaged.

Parameter	Symbol	Conditions	Ratings	Unit
Storage temperature			-65 to +150	°C
Supply voltage			-0.5 to 4.6	V
DC input voltage			-0.5 to V_{DD}+0.5	V
Overshoot voltage (below 20ns)			-1.0 to V_{DD}+1.0	V

Operating Conditions

Parameter	Symbol	Conditions	Ratings	Unit
Operating temperature (at read)			-40 to +85	°C
Operating temperature (at write)			-20 to +85	°C
Operating supply voltage			1.8 to 3.6	V

DC Electrical Characteristics

Parameter	Symbol	Conditions	min	typ	max	Unit
Supply current when reading	I_{CCR}	$\overline{CS}$ = 0.1V_{DD}, $\overline{HOLD}$ = $\overline{WP}$ = 0.9V_{DD} SI = 0.1V_{DD}/0.9V_{DD}, SO = Open Operating frequency = 3MHz, V_{DD} = 3.6V			3	mA
		$\overline{CS}$ = 0.1V_{DD}, $\overline{HOLD}$ = $\overline{WP}$ = 0.9V_{DD} SI = 0.1V_{DD}/0.9V_{DD}, SO = Open Operating frequency = 2MHz, V_{DD} = 2.5V			2	mA
Supply current when writing	I_{CCW}	V_{DD} = V_{DD} Max			3	mA
CMOS standby current	I_{SB}	V_{IN} = V_{DD} or V_{SS}, V_{DD} = V_{DD} Max			2	μA
Input leakage current	I_{LI}	V_{IN} = V_{SS} to V_{DD}, V_{DD} = V_{DD} max.	-2		2	μA
Output leakage current	I_{LO}	V_{IN} = V_{SS} to V_{DD}, V_{DD} = V_{DD} max.	-2		2	μA

Input low voltage	V_{IL}	V_{DD} = V_{DD} max.	-0.3		0.3V_{DD}	V
Input high voltage	V_{IH}	V_{DD} = V_{DD} min.	0.7V_{DD}		V_{DD}+0.3	V
Output low voltage	V_{OL1}	I_{OL} = 1.5mA, V_{DD} = 3.6V			0.4	V
	V_{OL2}	I_{OL} = 0.15mA, V_{DD} = 1.8V			0.2	V
Output high voltage	V_{OH1}	I_{OH} = -0.4mA, V_{DD} = 3.6V	0.8V_{DD}			V
	V_{OH2}	I_{OH} = -0.2mA, V_{DD} = 1.8V	0.8V_{DD}			V

Capacitance at Ta = 25°C, f = 1.0MHz

Parameter	Symbol	Conditions	min	typ	max	Unit
Output pin capacitance	C_{DQ}	V_{DQ} = 0V			12	pF
Input pin capacitance	C_{IN}	V_{IN} = 0V			6	pF

Note : These parameters are sampled and not 100% tested.

AC Electrical Characteristics

Input pulse level	0.2×V_{DD} to 0.8×V_{DD}
Input pulse rise/fall time	10ns
Output detection voltage	0.5×V_{DD}
Output load	30pF

AC Characteristics (at FCLK = 3MHz)/V_{DD} = 2.5V to 3.6V

Parameter	Symbol	Conditions	min	typ	max	Unit
Clock frequency	FCLK				3	MHz
SCK logic high level pulse width	t_{CLHI}		100			ns
SCK logic low level pulse width	t_{CLLO}		100			ns
Input signal rise/fall time	t_{RF}				1	us
$\overline{CS}$ setup time	t_{CSS}		100			ns
SCK setup time	t_{CLS}		100			ns
Data setup time	t_{DS}		30			ns
Data hold time	t_{DH}		50			ns
$\overline{CS}$ hold time	t_{CSH}		100			ns
SCK hold time	t_{CLH}		150			ns
$\overline{CS}$ standby pulse width	t_{CPH}		100			ns
$\overline{CS}$ output high impedance time	t_{CHZ}				150	ns
SCK output data time	t_V				120	ns
Output data hold time	t_{HO}		0			ns
$\overline{WP}$ setup time	t_{WPS}		30			ns
$\overline{WP}$ hold time	t_{WPH}		30			ns
$\overline{HOLD}$ setup time	t_{HS}		30			ns
$\overline{HOLD}$ hold time	t_{HH}		30			ns
$\overline{HOLD}$ output low impedance time	t_{HLZ}				150	ns
$\overline{HOLD}$ output high impedance time	t_{HHZ}				300	ns
Write cycle time	t_{WC}				10	ms
SCK output low impedance time	t_{CLZ}		0			ns

AC Characteristics (at FCLK = 2MHz)/V_{DD} = 1.8V to 3.6V

Parameter	Symbol	Conditions	min	typ	max	Unit
Clock frequency	FCLK				2	MHz
SCK logic high level pulse width	t_{CLHI}		200			ns
SCK logic low level pulse width	t_{CLLO}		200			ns
Input signal rise/fall time	t_{RF}				1	us
$\overline{CS}$ setup time	t_{CSS}		200			ns
SCK setup time	t_{CLS}		200			ns
Data setup time	t_{DS}		40			ns
Data hold time	t_{DH}		50			ns
$\overline{CS}$ hold time	t_{CSH}		200			ns
SCK hold time	t_{CLH}		200			ns
$\overline{CS}$ standby pulse width	t_{CPH}		200			ns
$\overline{CS}$ output high impedance time	t_{CHZ}				250	ns
SCK output data time	t_V				150	ns
Output data hold time	t_{HO}		0			ns
$\overline{WP}$ setup time	t_{WPS}		30			ns
$\overline{WP}$ hold time	t_{WPH}		30			ns
$\overline{HOLD}$ setup time	t_{HS}		30			ns
$\overline{HOLD}$ hold time	t_{HH}		30			ns
$\overline{HOLD}$ output low impedance time	t_{HLz}				250	ns
$\overline{HOLD}$ output high impedance time	t_{HHz}				300	ns
Write cycle time	t_{WC}				10	ms
SCK output low impedance time	t_{CLZ}		0			ns

Table 1 Command Settings

Command	1st bus cycle	2nd bus cycle	3rd bus cycle	4th bus cycle	5th bus cycle	6th bus cycle	nth bus cycle
Write enable (WREN)	06h						
Write disable (WRDI)	04h						
Status register read (RDSR)	05h						
Status register write (WRSR)	01h	DATA					
Read (READ)	03h	A15-A8	A7-A0				
Write (WRITE)	02h	A15-A8	A7-A0	PD *1	PD *1	PD *1	PD *1

Explanatory notes for Table 1

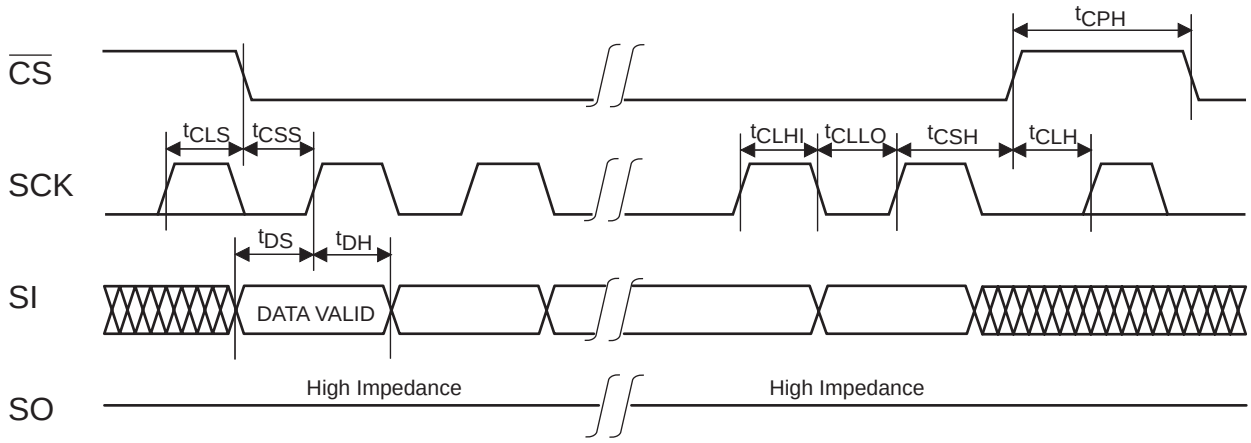
The “h” following each code indicates that the number given is in hexadecimal notation.

Addresses A15 - A13 for all commands are “don’t care.”

*1: “PD” stands for page program data. Any amount of data from 1 to 32 bytes is input.

Figure 2 Serial Input Timing

(SPI Mode 0)



(SPI Mode 3)

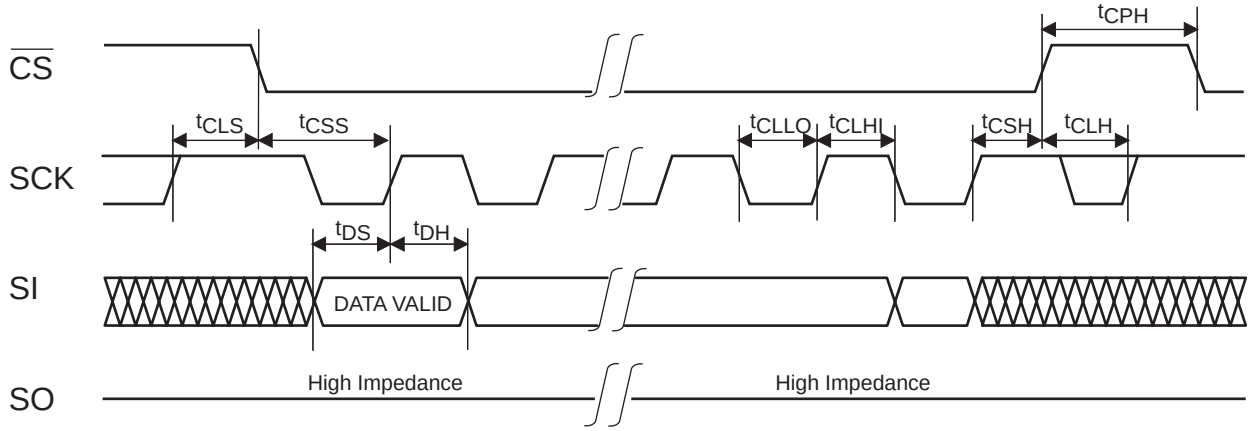
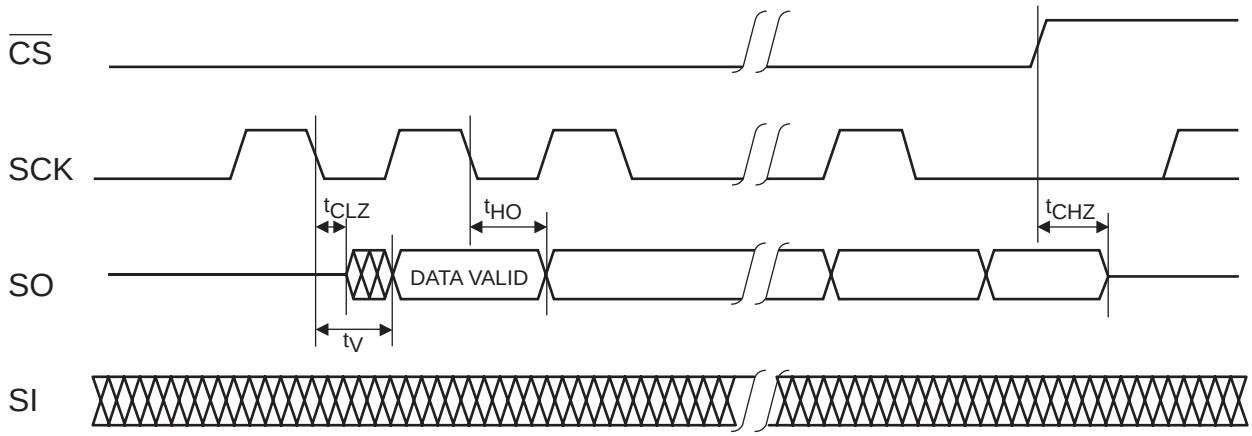
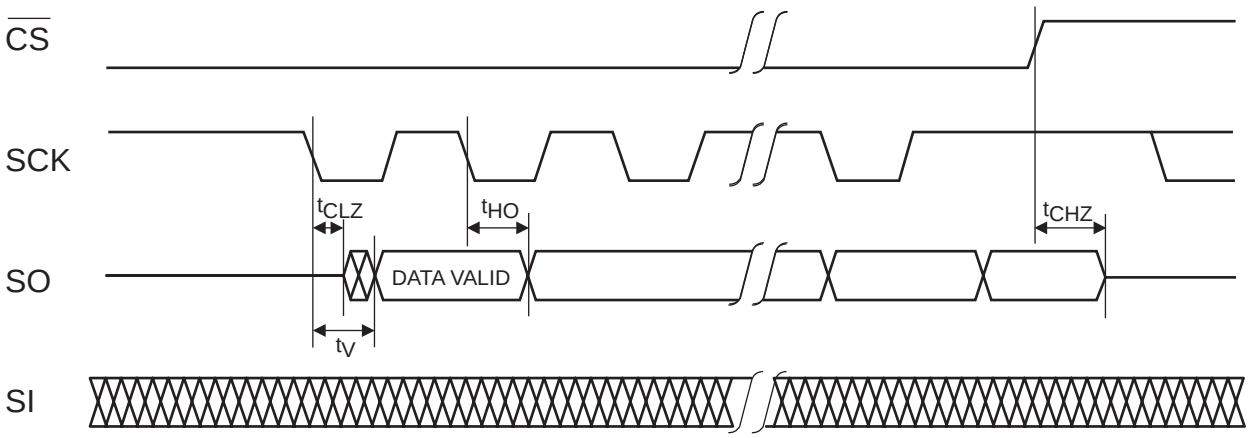


Figure 3 Serial Output Timing

(SPI Mode 0)



(SPI Mode 3)



Description of Commands and Their Operations

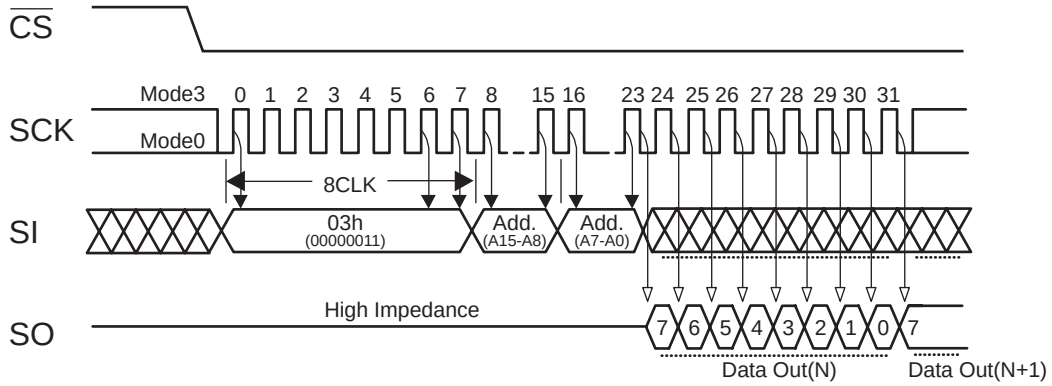
"Table 1 Command Settings" provides a list and overview of the commands. A detailed description of the functions and operations corresponding to each command is presented below.

1. Read (READ)

Consisting of the first through third bus cycles, the read command inputs the 16-bit addresses following (03h), and the data in the designated addresses is output synchronized to SCK. The data is output from SO on the falling edge of third bus cycle bit0 as a reference. "Figure 4 READ" shows the timing waveforms.

When SCK is input continuously after the read command has been input and the data in the designated addresses has been output, the address is automatically incremented inside the device while SCK is being input, and the corresponding data is output in sequence. If the SCK input is continued after the internal address arrives at the highest address, the internal address returns to the lowest address (0000h), and data output is continued. By setting the logic level of $\overline{CS}$ to high, the device is deselected, and the read cycle ends. While the device is deselected, the output pin SO is in a high-impedance state.

Figure 4 READ



- Addresses A15 - A13 are "don't care."
- In synchronization with the rising edges of 0 to 23 clock signals, the command is identified and the addresses are taken in through SI.
- In synchronization with the falling edges of 23 clock signal or later, the data is output to SO.

2. Status Registers

The status registers read the operating and setting statuses inside the device from outside (status register read) and set the protect information (status register write). There are 8 bits in total, and “Table 2 Status Registers” gives the significance of each bit.

Table 2 Status Registers

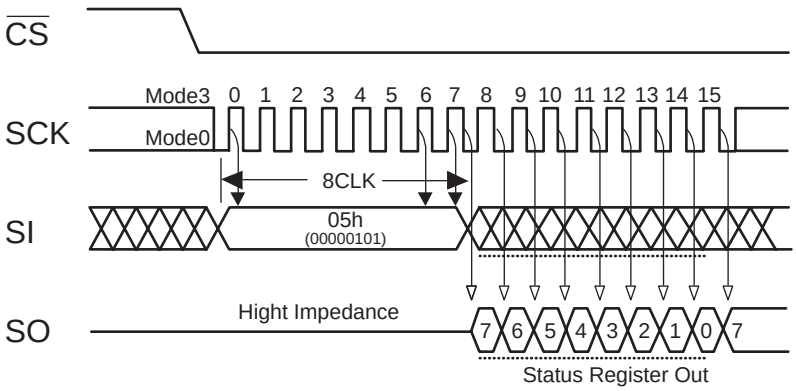
Bit	Name	Logic	Function	Power-on time Information
Bit0	$\overline{RDY}$	0	Ready	0
		1	Busy (in write operation)	
Bit1	WEN	0	Write disabled	0
		1	Write enabled	
Bit2	BP0	0	Block protect information See status register description on BP0 and BP1	Nonvolatile information
		1		
Bit3	BP1	0		Nonvolatile information
		1		
Bit4	×	0	Reserved bit	0
Bit5	×	0	Reserved bit	0
Bit6	×	0	Reserved bit	0
Bit7	SRWP	0	Status register write enabled	Nonvolatile information
		1	Status register write disabled	

2-1. Status Register Read (RDSR)

The contents of the status registers can be read using the status register read command. This command can be executed even during write operation.

“Figure 5 Status Register READ” shows the timing waveforms of status register read. Consisting only of the first bus cycle, the status register command outputs the contents of the status registers synchronized to the falling edge of the clock (SCK) with which the eighth bit of (05h) has been input. In terms of the output sequence, SRWP (bit7) is the first to be output, and each time one clock is input, all the other bits up to $\overline{RDY}$ (bit0) are output in sequence, synchronized to the falling clock edge. If the clock input is continued after $\overline{RDY}$ (bit0) has been output, the data is output by returning to the bit (SRWP) that was first output, after which the output is repeated as long as the clock input is continued. The data can be read by the status register read command at any time.

Figure 5 Status Register Read

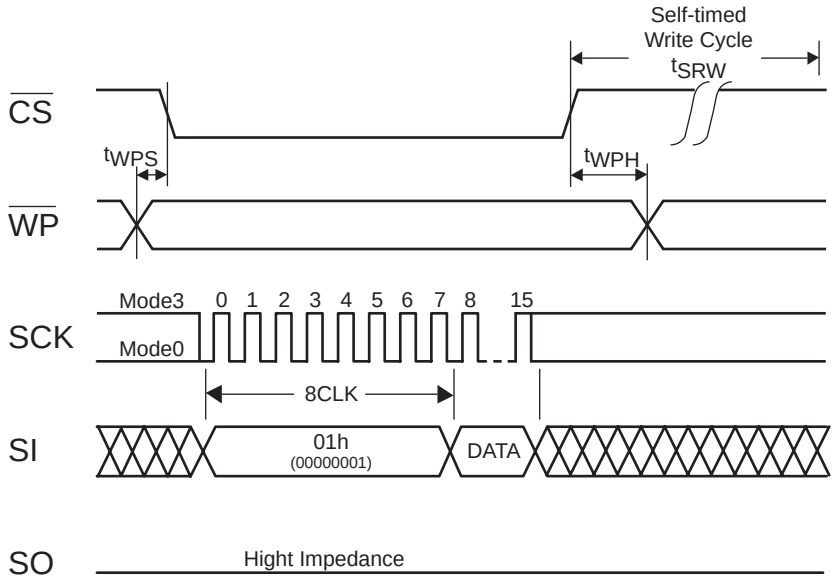


2-2. Status Register Write (WRSR)

The information in status registers BP0, BP1, and SRWP can be rewritten using the status register write command. $\overline{RDY}$, WEN, bit4, bit5, and bit6 are read-only bits and cannot be rewritten. The information in bits BP0, BP1, and SRWP is stored in the non-volatile memory, and when it is written in these bits, the contents are retained even at power-down.

"Figure 6 Status Register Write" shows the timing waveforms of status register write, and Figure 11 shows a status register write flowchart. Consisting of the first and second bus cycles, the status register write command initiates the internal write operation at the rising $\overline{CS}$ edge after the data has been input following (01h). By the operation of this command, the information in bits BP0, BP1, and SRWP can be rewritten. Since bits $\overline{RDY}$ (bit0), WEN (bit1), bit4, bit5, and bit6 of the status register cannot be written, no problem will arise if an attempt is made to set them to any value when rewriting the status register. Status register write ends can be detected by $\overline{RDY}$ of status register read. Information in the status register can be rewritten 1,000 times (min.). To initiate status register write, the logic level of the $\overline{WP}$ pin must be set high and the status register WEN must be set to "1".

Figure 6 Status Register Write



2-3. Contents of Each Status Register

$\overline{RDY}$ (bit0) **Ready/Busy detection**

The $\overline{RDY}$ register is for detecting the write end. When it is "1", the device is in a busy state, and when it is "0", it means that the write operation is completed.

WEN (bit1) **Write enable**

The WEN register is for detecting whether the device can perform write operations. If it is set to "0", the device will not perform the write operation even if the write command is input. If it is set to "1", the device can perform write operation in any area that is not block-protected.

WEN can be controlled using the write enable and write disable commands. By inputting the write enable command (06h), WEN can be set to "1", and by inputting the write disable command (04h), it can be set to "0". In the following states, WEN is automatically set to "0" in order to protect against unintentional writing.

- At power-on
- Upon completion of write
- Upon completion of status register write

∗ If a write operation has not been performed inside the device because, for instance, the command input for any of the write operations has failed or a write operation has been performed for a protected address, WEN will retain the status established prior to the issue of the command concerned. Furthermore, its state will not be changed by a read operation.

BP0, BP1 (bits2, 3) **Block Protect Settings**

Block protect BP0 and BP1 are status register bits that can be rewritten, and the memory space to be protected can be set depending on these bits. For the setting conditions, refer to “Table 3 Protect Level Setting Conditions.”

Table 3 Protect Level Setting Conditions

Protection Block (Level)	Status Register Bits		Protected Area
	BP1	BP0	
0 (Whole area unprotected)	0	0	None
1 (Upper 1/4 area protected)	0	1	1800h to 1FFFh
2 (Upper 1/2 area protected)	1	0	1000h to 1FFFh
3 (Whole area protected)	1	1	0000h to 1FFFh

SRWP (bit7) **Status Register Write Protect Settings**

Status register write protect SRWP is the bit for protecting the status registers, and its information can be rewritten. When SRWP is “1” and the logic level of the $\overline{WP}$ pin is low, the status register write command is ignored, and status registers BP0, BP1, BP2, and SRWP are protected. When the logic level of the $\overline{WP}$ pin is high, the status registers are not protected regardless of the SRWP state. The SRWP setting conditions are shown in “Table 4 SRWP Setting Conditions.”

Table 4 SRWP Setting Conditions

$\overline{WP}$ Pin	SRWP	Mode	Status Register	Protected Area	Unprotected Area
1	0	Software protected (SPM)	Unprotected	Protected	Unprotected
0	0				
1	1				
0	1	Hardware protected (HPM)	Protected	Protected	Unprotected

Bit4, bit5, and bit6 are reserved bits, and have no significance.

3. Write Enable (WREN)

Before performing any of the operations listed below, the device must be placed in the write enable state. Operation is the same as for setting status register WEN to “1”, and the state is enabled by inputting the write enable command. “Figure 7 Write Enable” shows the timing waveforms when the write enable operation is performed. The write enable command consists only of the first bus cycle, and it is initiated by inputting (06h).

- Write (WRITE)
- Status register write (WRSR)

4. Write Disable (WRDI)

The write disable command sets status register WEN to “0” to prohibit unintentional writing. “Figure 8 Write Disable” shows the timing waveforms. The write disable command consists only of the first bus cycle, and it is initiated by inputting (04h).

The write disable state (WEN “0”) is exited by setting WEN to “1” using the write enable command (06h).

Figure 7 Write Enable

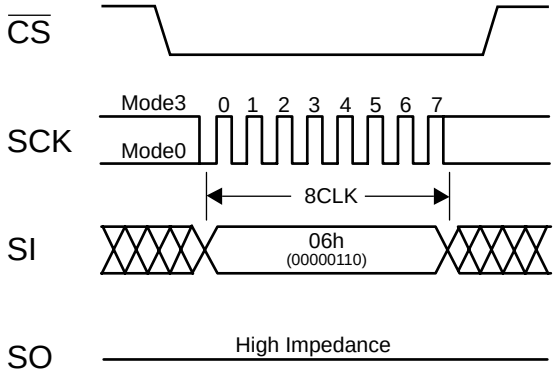
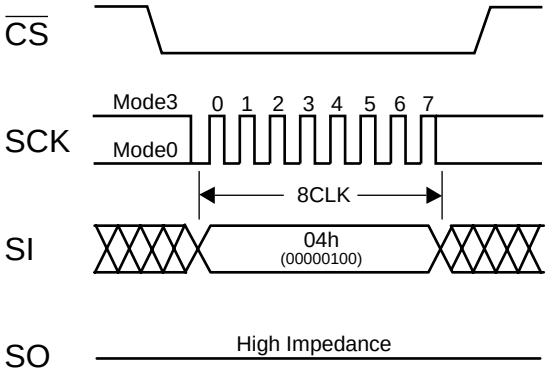


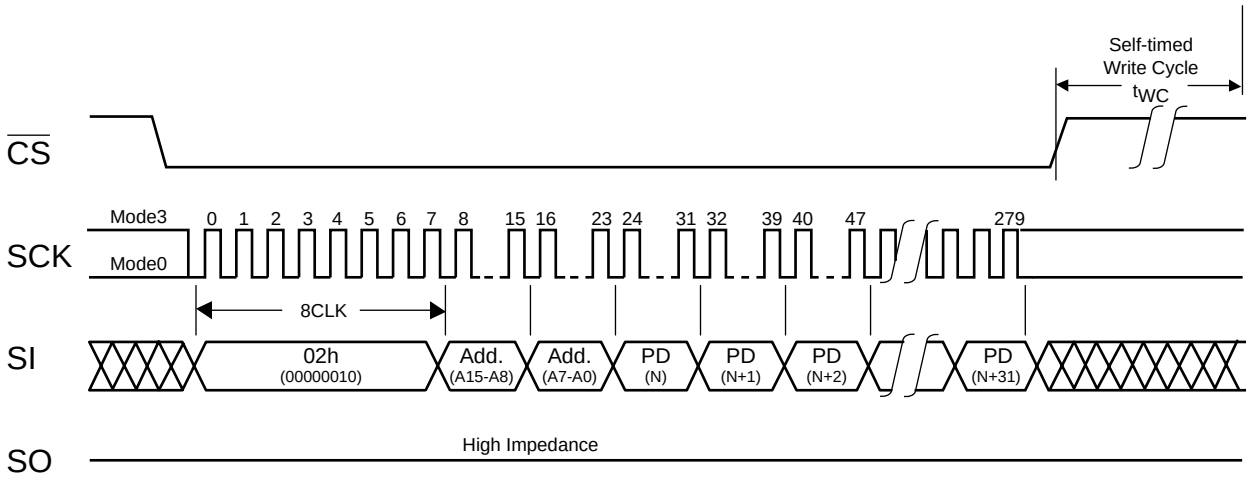
Figure 8 Write Disable



5. Write (WRITE)

The LE25LA642CS enables pages with up to 32bytes to be written. Any number of bytes from 1 to 32bytes can be written within the same sector page (page addresses : A15 to A5). “Figure 9 Write” shows the write timing waveforms, and Figure 12 shows a write flowchart. After the falling $\overline{CS}$ edge, the command (02H) is input followed by the 16-bit addresses (Add). The write data is then loaded until the rising $\overline{CS}$ edge, and the internal addresses (A4 to A0) are incremented (Add+1) every time the data is loaded in 1-byte increments. The data loading continues until the rising $\overline{CS}$ edge. If the data loaded has exceeded 32bytes, the 32bytes loaded last are written. The write data must be loaded in 1-byte increments, and the write operation is not performed at the rising $\overline{CS}$ edge occurring at any other timing. The write time is 10ms (max.) when 32bytes (1page) are written at one time.

Figure 9 Write

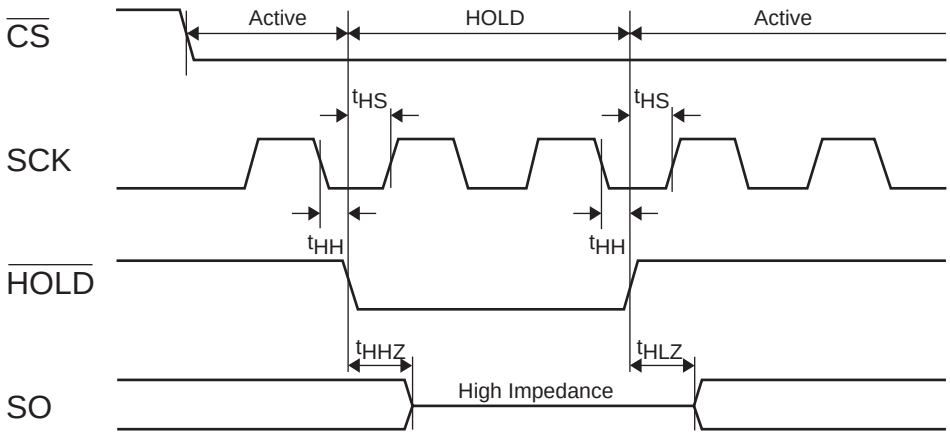


- Addresses A15 - A13 are “don’t care.”

6. Hold Function

Using $\overline{HOLD}$ pin, the hold function suspends serial communication (it places it in the hold status). “Figure 10 $\overline{HOLD}$” shows the timing waveforms. The device is placed in the hold status at the falling $\overline{HOLD}$ edge while the logic level of SCK is low, and it exits from the hold status at the rising $\overline{HOLD}$ edge. When the logic level of SCK is high, $\overline{HOLD}$ must not rise or fall. The hold function takes effect when the logic of $\overline{CS}$ is low, and the hold status is exited and serial communication is reset at the rising $\overline{CS}$ edge. In the hold status, the SO output is in the high-impedance state, and SI and SCK are “don’t care.”

Figure 10 $\overline{HOLD}$



7. Hardware Data Protection

In order to protect against unintentional writing at power-on, the LE25LA642CS incorporates a power-on reset function.

8. Software Data Protection

This product eliminates the possibility of unintentional operations by not recognizing commands under the following conditions.

- When a write command is input and the rising $\overline{CS}$ edge timing is not in a bus cycle (8CLK units of SCK).
- When the write data is not in 1-byte increments.
- When the status register write command is input for 2bus cycles or more.

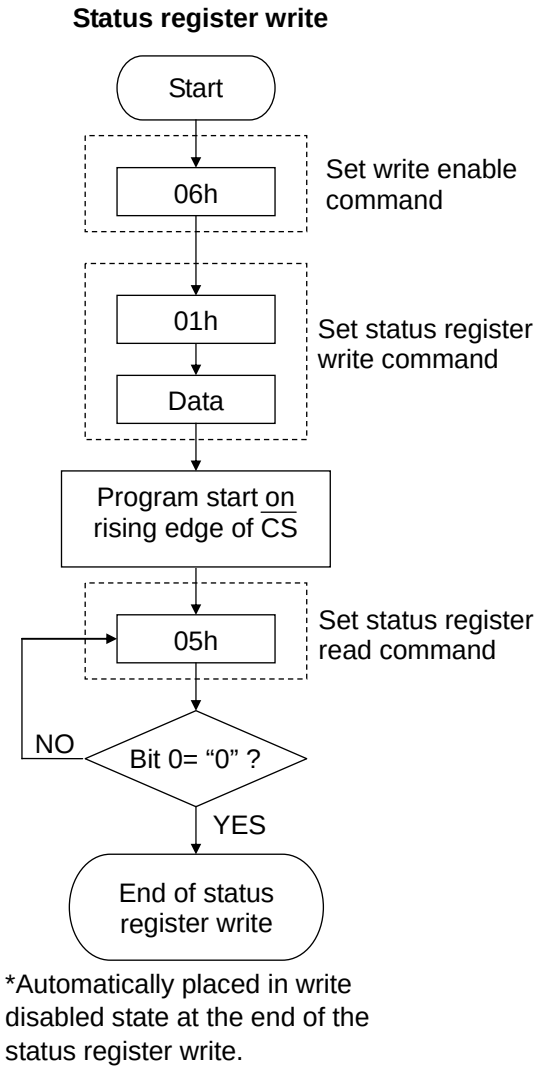
9. Power-on

In order to protect against unintentional writing, $\overline{CS}$ must be kept at V_{DD} at power-on. After power-on, the supply voltage has stabilized at 1.8V or higher, wait for 10μs (t_{PU_READ}) before inputting the command to start a read operation. Similarly, wait for 10ms (t_{PU_WRITE}) after the supply voltage has stabilized at 1.8V or higher before inputting the command to start a write operation.

10. Decoupling Capacitor

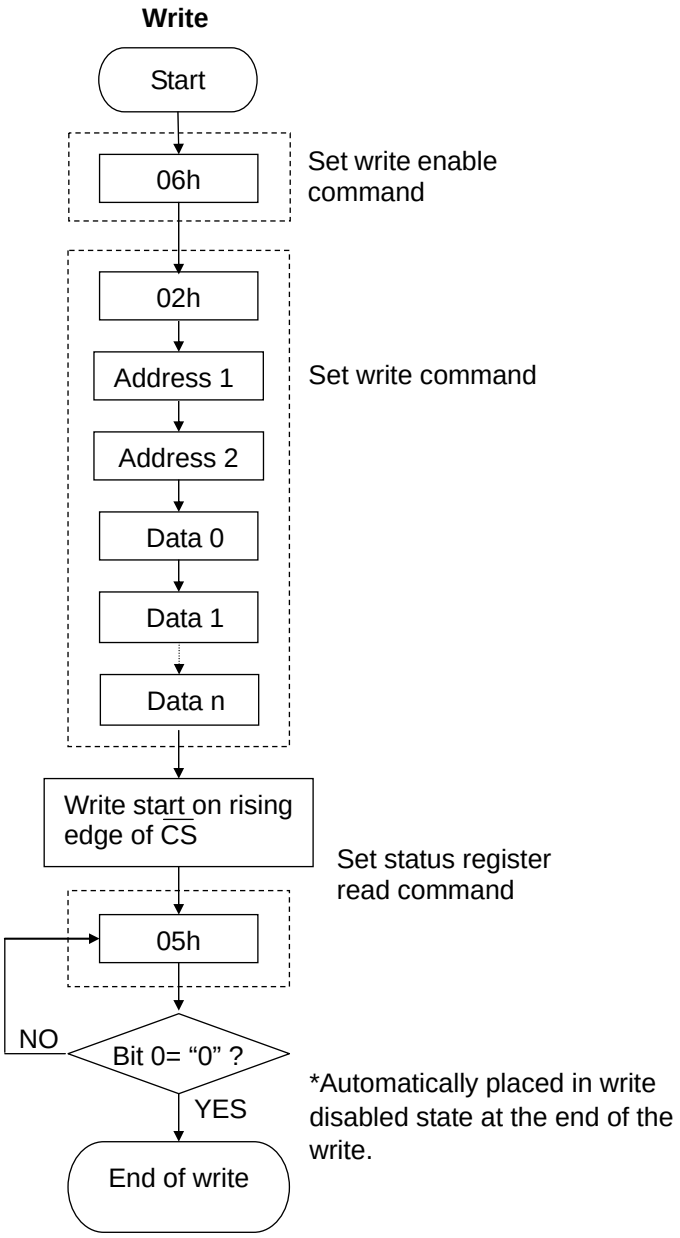
A0.1μF ceramic capacitor must be provided to each device and connected between V_{DD} and V_{SS} in order to ensure that the device will operate stably.

Figure 11 Status Register Write Flowchart



*Automatically placed in write disabled state at the end of the status register write.

Figure 12 Write Flowchart



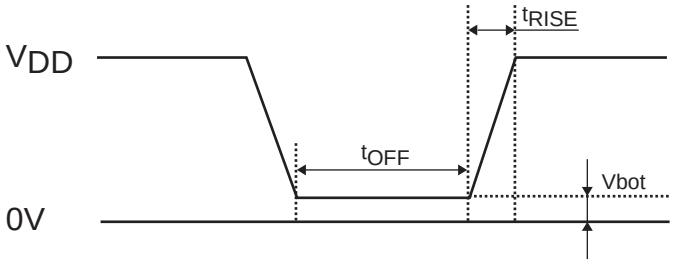
*Automatically placed in write disabled state at the end of the write.

Application Note

1) Precautions at Power-on

In order to protect against unintentional writing, the LE25LA642CS incorporates a power-on rest circuit. The following conditions must be met in order to ensure that the power-on reset circuit will operate stably. No guarantees are given for data in the event of an instantaneous power failure occurring during the write operation.

Symbol	Item	V_{DD} = 1.8 to 3.6V			Unit
		min	typ	max	
t_{RISE}	Power rise time			100	ms
t_{OFF}	Power off time	10			ms
Vbot	Power bottom voltage			0.2	V



Note:
1). The $\overline{CS}$ pin must be set high.